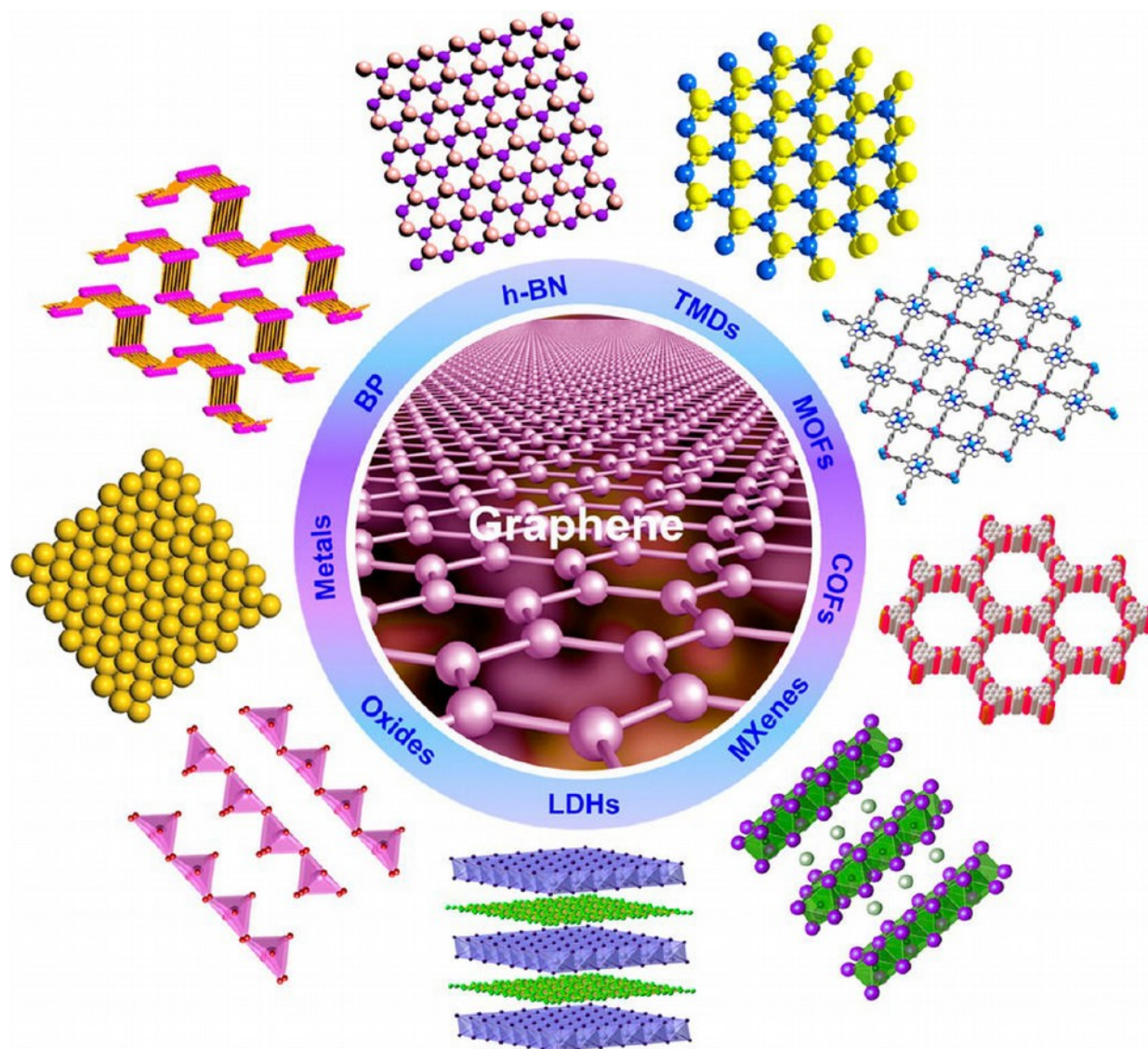


Prediction of Large-Gap Topological Insulator in functionalized Ordered Double Transition Metal MXene

Zhi-Quan Huang¹, Mei-Ling Xu¹, Gennevieve Macam¹,
Chia-Hsiu Hsu¹ and Feng-Chuan Chuang¹

1 Department of Physics, National Sun Yat-Sen University

Different kinds of typical ultrathin 2D nanomaterials

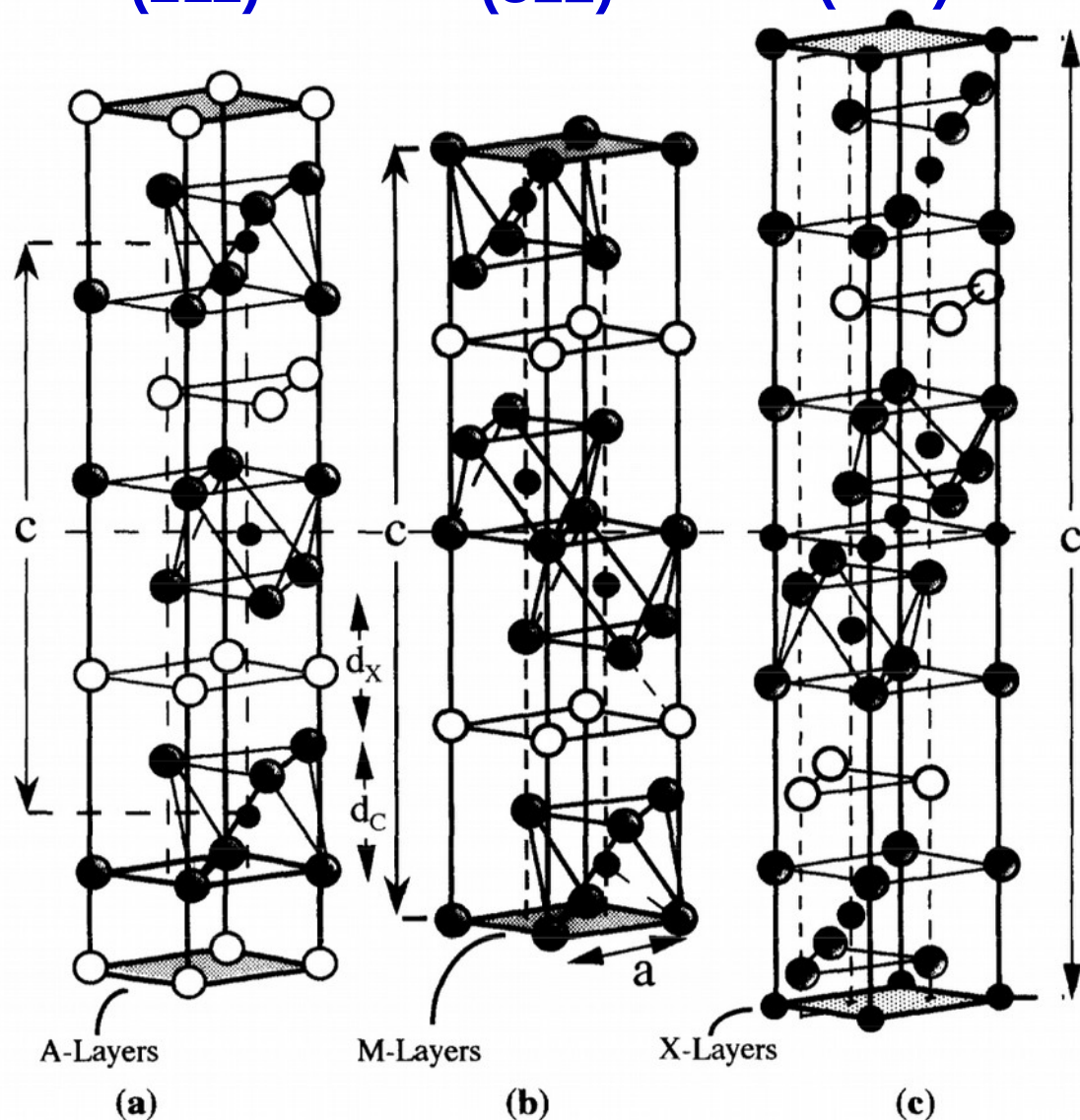


$M_{n+1}AX_n$ Structure

M_2AX_1
(211)

M_3AX_2
(312)

M_4AX_3
(413)



$M_{n+1}AX_n$

n : 1, 2 or 3

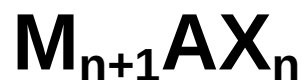
M : early transition metal

A : A-group (mostly IIIA and IVA) element

X : C or N.

Table of $M_{n+1}AX_n$

IIB	IIIA	IVA	VA	VIA
	Al Ti₂AlC, 4.11 (3.04,13.60) V₂AlC, 4.07 (3.1,13.83) Cr₂AlC, 5.24 (2.86,12.8) Nb₂AlC, 6.50 (3.10,13.8) Ta₂AlC, 11.82 (3.07,13.8) Ti₂AlN, 4.31 (2.989,13.614) Ti₃AlC₂, 4.5 (3.075,18.578) Ti₄AlN₃, 4.76 (2.988, 23.372)	Si Ti₃SiC₂, 4.52 (3.0665,17.671)	P V₂PC, 5.38 (3.077,10.91) Nb₂PC, 7.09 (3.28,11.5)	S Ti₂SC, 4.62 (3.216,11.22) Zr₂SC, 6.20 (3.40, 12.13) Nb₂SC_{0.4}, 3.27 ,11.4) Hf₂SC, 3.36 , 11.99)
Zn	Ga Ti₂GaC, 5.53 (3.07, 13.52) V₂GaC, 6.39 (2.93, 12.84) Cr₂GaC, 6.81 (2.88, 12.61) Nb₂GaC, 7.73 (3.13, 13.56) Mo₂GaC, 8.79 (3.01, 13.18) Ta₂GaC, 13.05 (3.10, 13.57) Ti₂GaN, 5.75 (3.00, 13.3) Cr₂GaN, 6.82 (2.875, 12.77) V₂GaN, 5.94 (3.00, 13.3)	Ge Ti₂GeC, 5.68 (3.07, 12.93) V₂GeC, 6.49 (3.00, 12.25) Cr₂GeC, 6.88 (2.95, 12.08) Ti₃GeC₂, 5.55 (3.07, 17.76)	As V₂AsC, 6.63 (3.11, 11.3) Nb₂AsC, 8.025 (3.31, 11.9)	Se
Cd Ti₂CdC, 9.71 (3.1, 14.41)	In Sc₂InC Ti₂InC, 6.2 (3.13, 14.06) Zr₂InC, 7.1 (3.34, 14.91) Nb₂InC, 8.3 (3.17,14.37) Hf₂InC, 11.57 (3.30,14.73) Ti₂InN, 6.54 (3.07,13.97) Zr₂InN, 7.53 (3.27,14.83)	Sn Ti₂SnC, 6.36 (3.163,13.679) Zr₂SnC, 7.16 (3.3576, 14.57) Nb₂SnC, 8.4 (3.241,13.802) Hf₂SnC, 11.8 (3.320,14.388) Hf₂SnN, 7.72 (3.31,14.3)	Sb	Te
	Tl Ti₂TlC, 8.63 (3.15,13.98) Zr₂TlC, 9.17 (3.36,14.78) Hf₂TlC, 13.65 (3.32,14.62) Zr₂TlN, 9.60 (3.3,14.71)	Pb Ti₂PbC, 8.55 (3.20,13.81) Zr₂PbC, 9.2 3.38,14.66 Hf₂PbC, 12.13 (3.55,14.46)	Bi	



n : 1, 2 or 3

M : early transition metal

A : A-group (mostly IIIA and IVA) element

X : C or N.

$M_{n+1}AX_n$ Structure

M_2AX_1

M_3AX_2

M_4AX_3

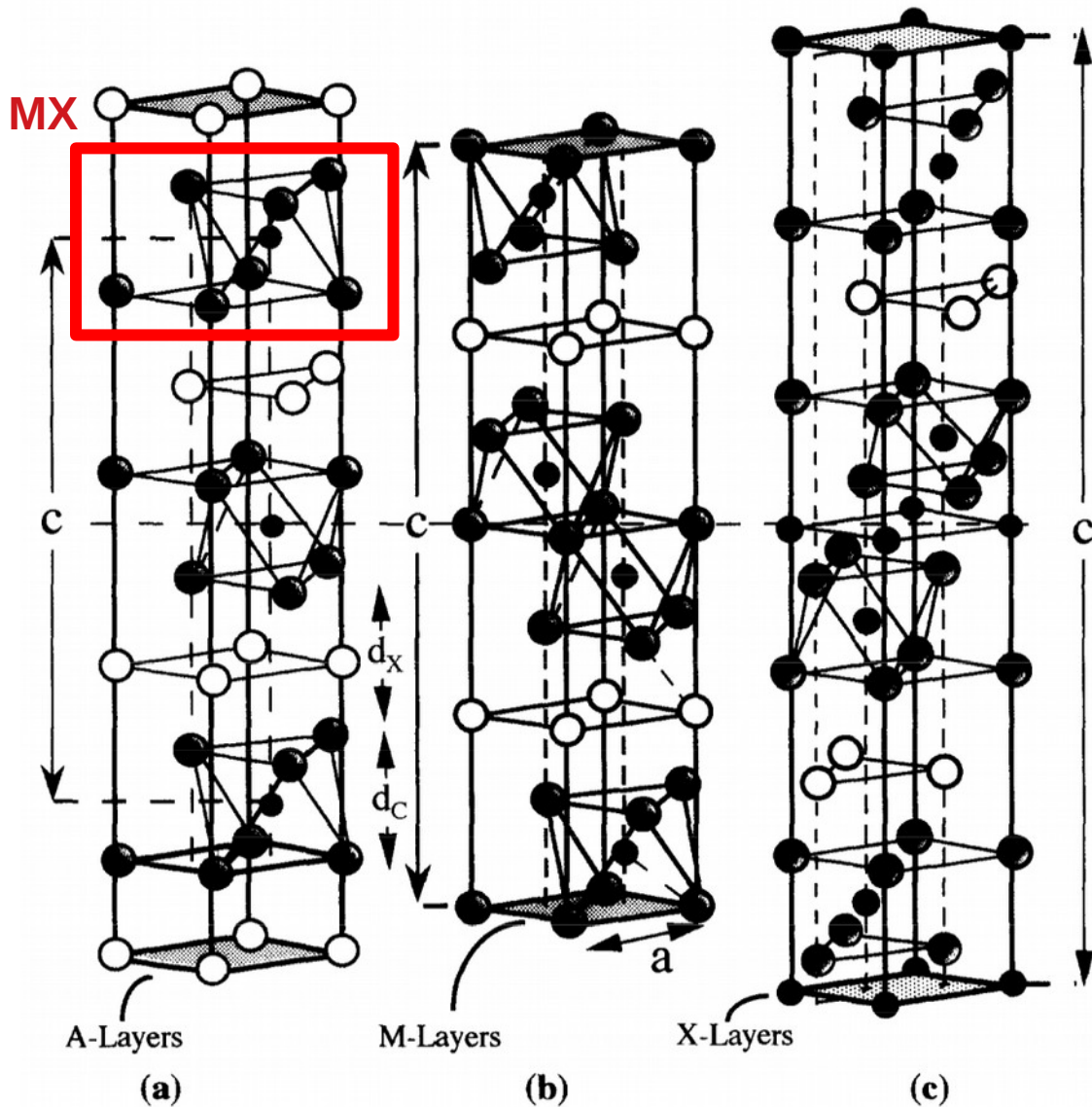
$M_{n+1}AX_n$

$n : 1, 2 \text{ or } 3$

M : early transition metal

A : A-group (mostly IIIA and IVA) element

X : C or N.

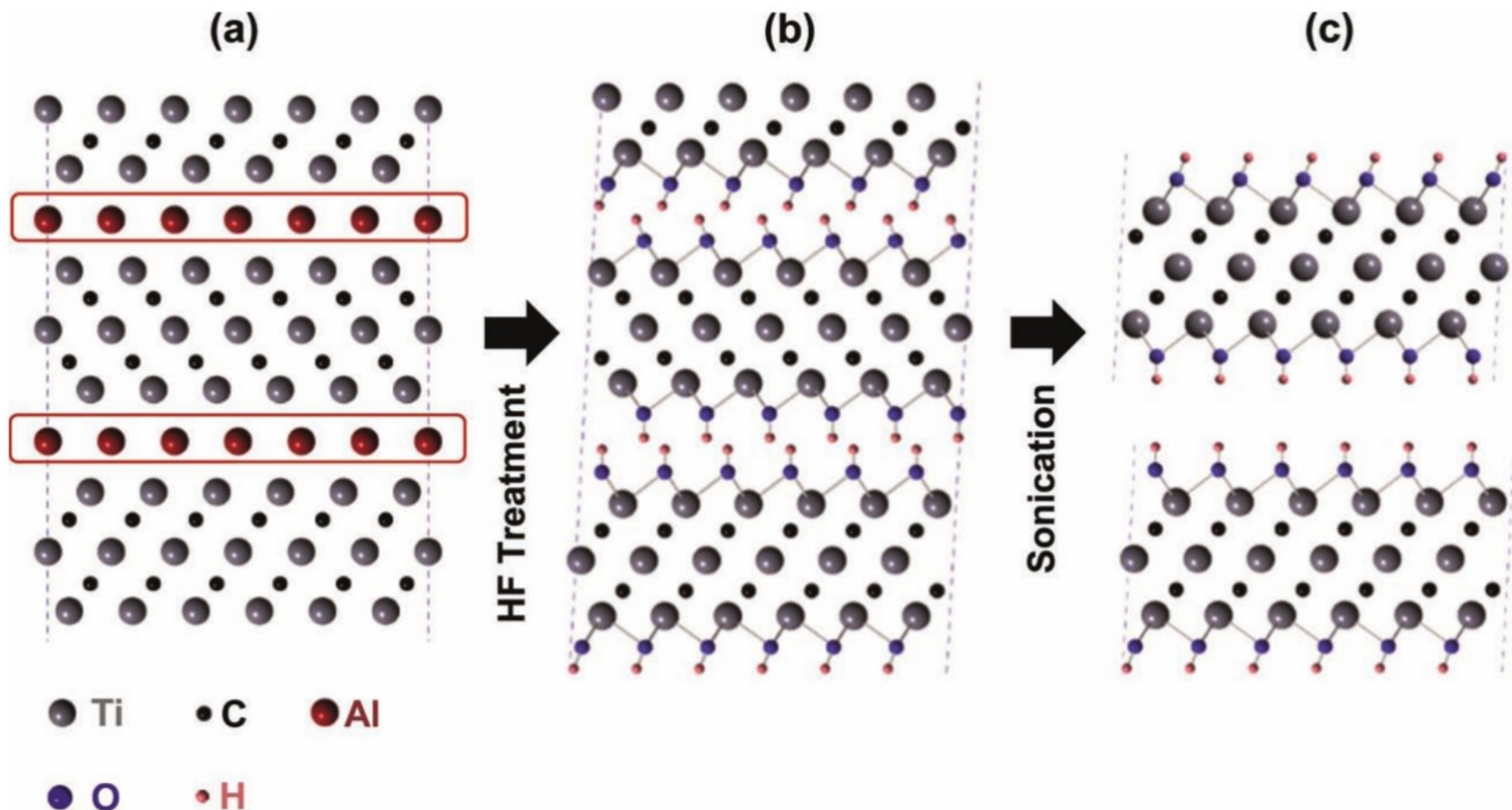


Two-Dimensional Nanocrystals Produced by Exfoliation of Ti_3AlC_2

Ti_3AlC_2 structure

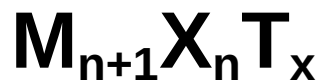
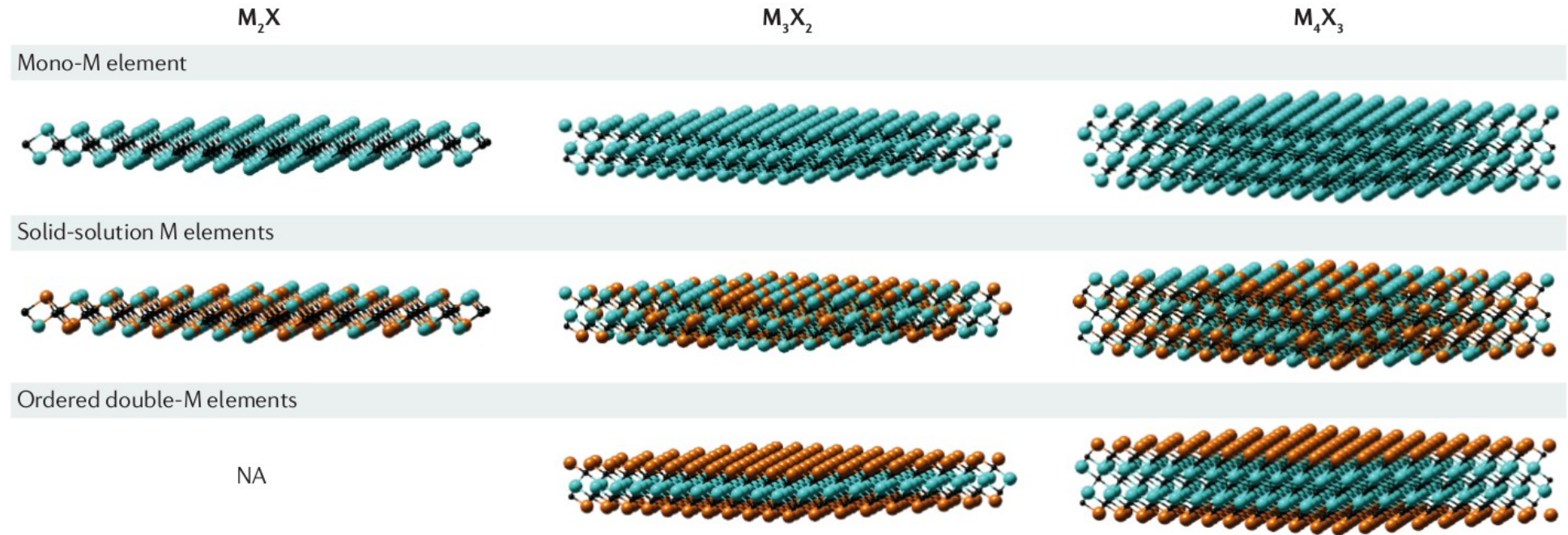
Al atoms
replaced by OH

Breakage of the hydrogen
bonds and separation



M. Naguib, M. Kurtoglu, V. Presser, J. Lu, J. Niu, M. Heon, L. Hultman, Y. Gogotsi, and M. W. Barsoum, *Advanced Materials* **23**, 4248 (2011).

MXene Structure



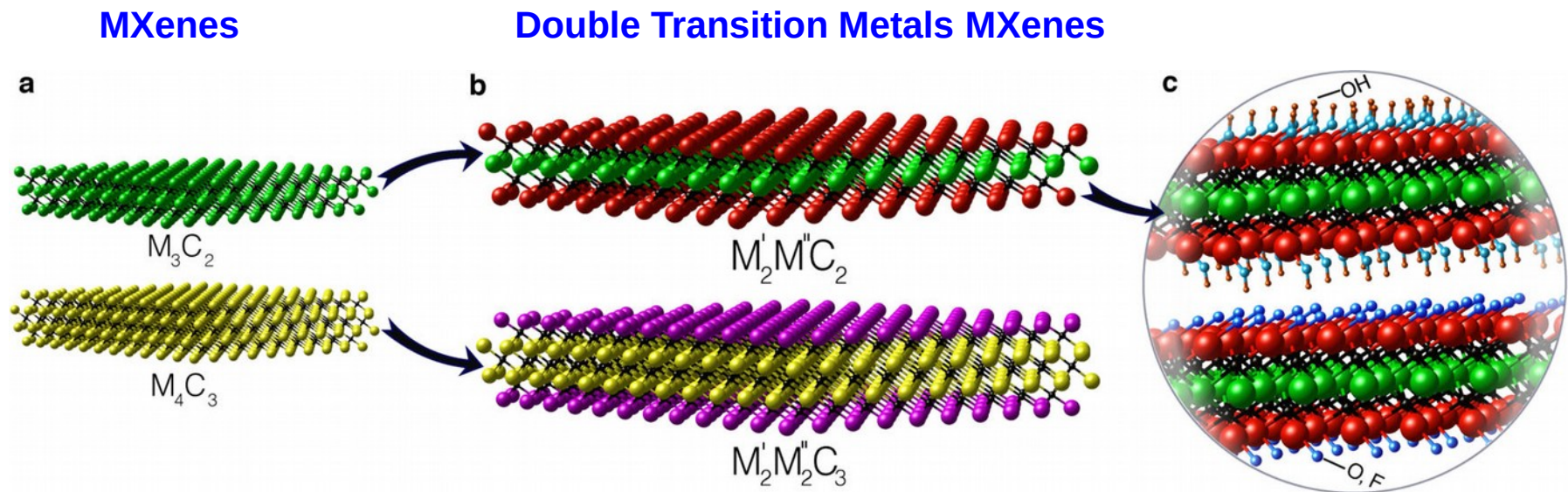
n : 1, 2 or 3

M : early transition metal

X : C or N

T : stands for the surface terminations (ex. H, O, F)

MXenes and Double Transition Metals MXenes



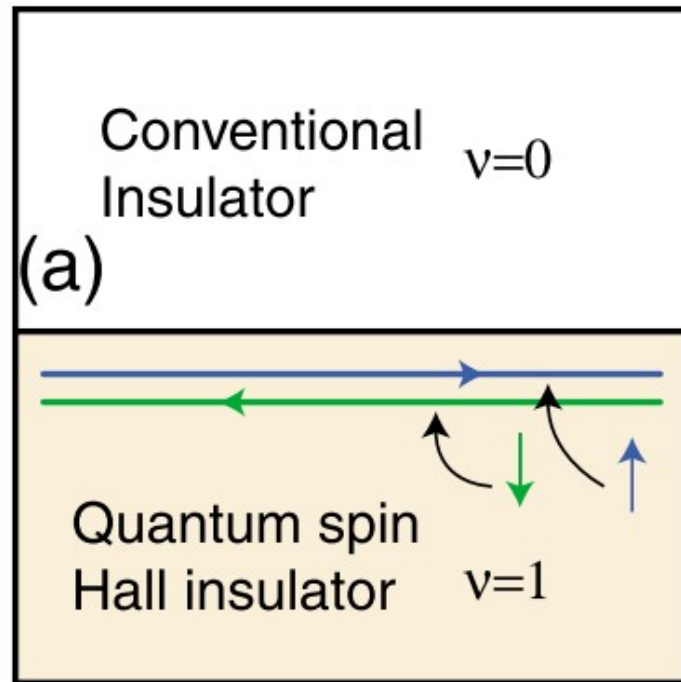
B. Anasori, Y. Xie, M. Beidaghi, J. Lu, B. C. Hosler, L. Hultman, P. R. C. Kent, Y. Gogotsi, and M. W. Barsoum, *ACS Nano* 9, 9507 (2015).

Sc ₂ C	Ti ₂ C	Ti ₂ N	Zr ₂ C	Ti ₃ C ₂	Ti ₃ N ₂	Ti ₃ (C,N) ₂	Zr ₃ C ₂	Ti ₄ N ₃	V ₄ C ₃	Nb ₄ C ₃	Ta ₄ C ₃
Zr ₂ N	Hf ₂ C	Hf ₂ N	V ₂ C	(Ti,V) ₃ C ₂	(Cr,V) ₃ C ₂	(Ti,Ta) ₂ C ₂	(Ti,Nb) ₂ C ₂	(Ti,Nb) ₄ C ₃	(Nb,Zr) ₄ C ₃	(Ti,Nb) ₂ C ₃	(Ti,Ta) ₂ C ₃
V ₂ N	Nb ₂ C	Ta ₂ C	Cr ₂ C	(Cr ₂ V) ₂ C ₂	(Mo ₂ V) ₂ C ₂	(Cr ₂ Nb) ₂ C ₂	(Cr ₂ Ta) ₂ C ₂	(V ₂ Ti) ₂ C ₃	(V ₂ Nb) ₂ C ₃	(V ₂ Ta) ₂ C ₃	(Nb ₂ Ta) ₂ C ₃
Cr ₂ N	Mo ₂ C	W ₂ C		(Mo ₂ Ti) ₂ C ₂	(Cr ₂ Ti) ₂ C ₂	(Mo ₂ Nb) ₂ C ₂	(Mo ₂ Ta) ₂ C ₂	(Cr ₂ Ti) ₂ C ₃	(Cr ₂ V) ₂ C ₃	(Cr ₂ Nb) ₂ C ₃	(Cr ₂ Ta) ₂ C ₃
(Ti,V) ₂ C	(Ti,Nb) ₂ C							(Mo ₂ Ti) ₂ C ₃	(Mo ₂ V) ₂ C ₃	(Mo ₂ Nb) ₂ C ₃	(Mo ₂ Ta) ₂ C ₃

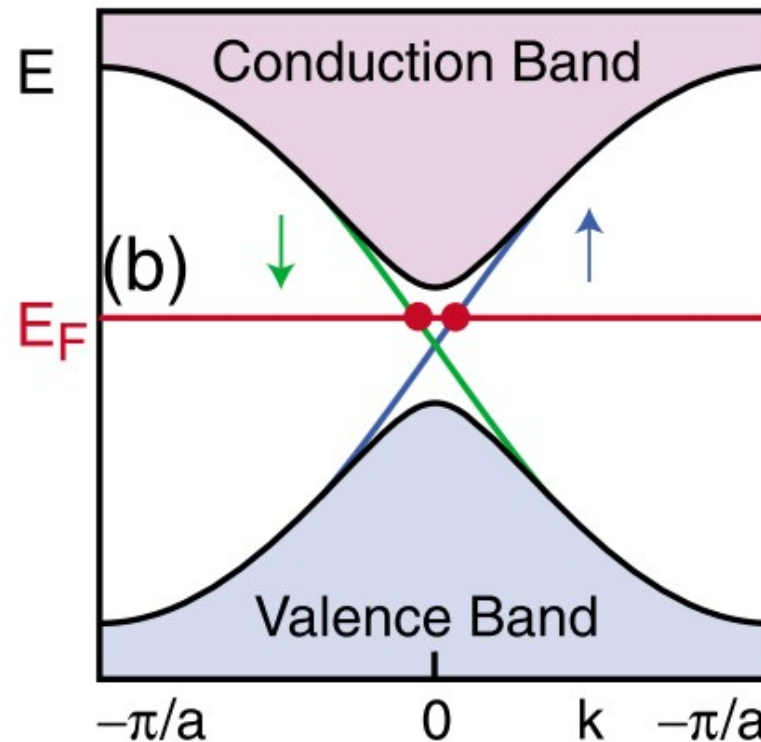
Experimental Theoretical Ordered double-M Solid-solution M

B. Anasori, M. R. Lukatskaya, and Y. Gogotsi, *Nature Reviews Materials* 2, 16098 (2017).

(2D) Topological insulators



- ν does not change without closing the gap.
- Quantum spin Hall edge states



- Protected by time-reversal symmetry
- No backscattering

Large-Gap Quantum Spin Hall State in MXenes: *d*-Band Topological Order in a Triangular Lattice

Chen Si,^{†,‡} Kyung-Hwan Jin,[§] Jian Zhou,[†] Zhimei Sun,^{*,†,‡} and Feng Liu[§]

[†]School of Materials Science and Engineering, Beihang University, Beijing 100191, China

[‡]Center for Integrated Computational Materials Engineering, International Research Institute for Multidisciplinary Science, Beihang University, Beijing 100191, China

[§]Department of Materials Science and Engineering, University of Utah, Salt Lake City, Utah 84112, United States

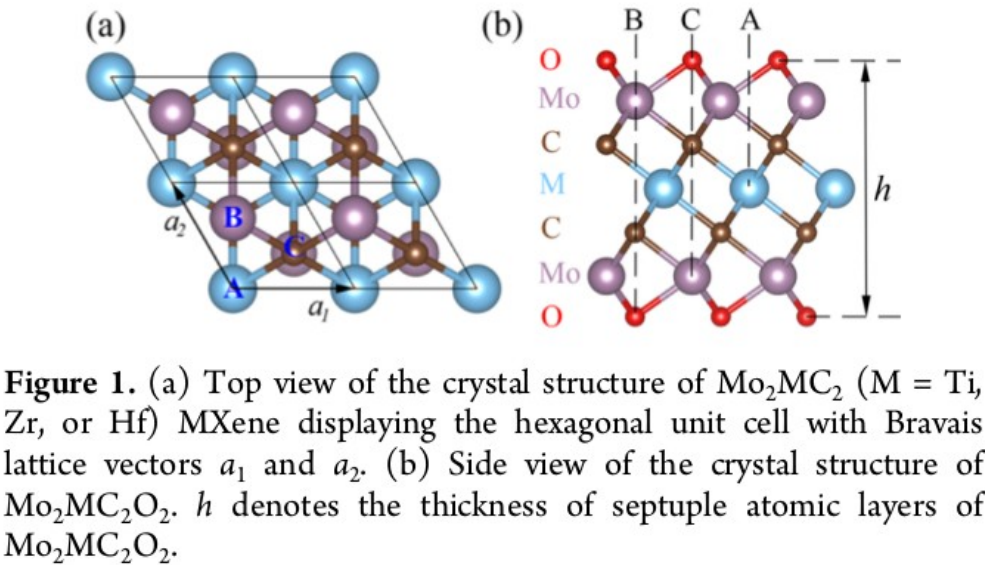


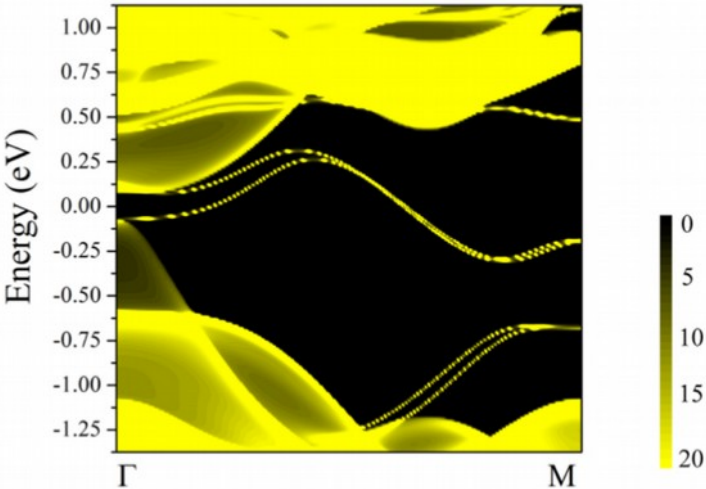
Figure 1. (a) Top view of the crystal structure of Mo₂MC₂ (M = Ti, Zr, or Hf) MXene displaying the hexagonal unit cell with Bravais lattice vectors a_1 and a_2 . (b) Side view of the crystal structure of Mo₂MC₂O₂. h denotes the thickness of septuple atomic layers of Mo₂MC₂O₂.

Table 1. Lattice Constants (a), Thickness (h), Nontrivial Gaps at the Γ Point (E_Γ), Indirect Bulk Gaps (E_{bulk}), and Z_2 Topological Invariants for Mo₂MC₂O₂^a

compound		Mo ₂ TiC ₂ O ₂	Mo ₂ ZrC ₂ O ₂	Mo ₂ HfC ₂ O ₂
a (Å)		2.94	3.02	3.01
h (Å)		7.59	7.79	7.75
E_Γ (eV)	GGA	0.052	0.087	0.213
	HSE06	0.125	0.147	0.301
E_{bulk} (eV)	GGA	0.041	0.066	0.154
	HSE06	0.096	0.105	0.201
Z_2		1	1	1

^aThe values of E_Γ and E_{bulk} calculated by GGA and HSE06 are all shown for comparison.

**Mo₂HfC₂O₂
on the zigzag edge**



Topological insulators in the ordered double transition metals $M'_2M''C_2$ MXenes ($M' = \text{Mo, W}$; $M'' = \text{Ti, Zr, Hf}$)

Mohammad Khazaei,^{1,*} Ahmad Ranjbar,¹ Masao Arai,² and Seiji Yunoki^{1,3,4}

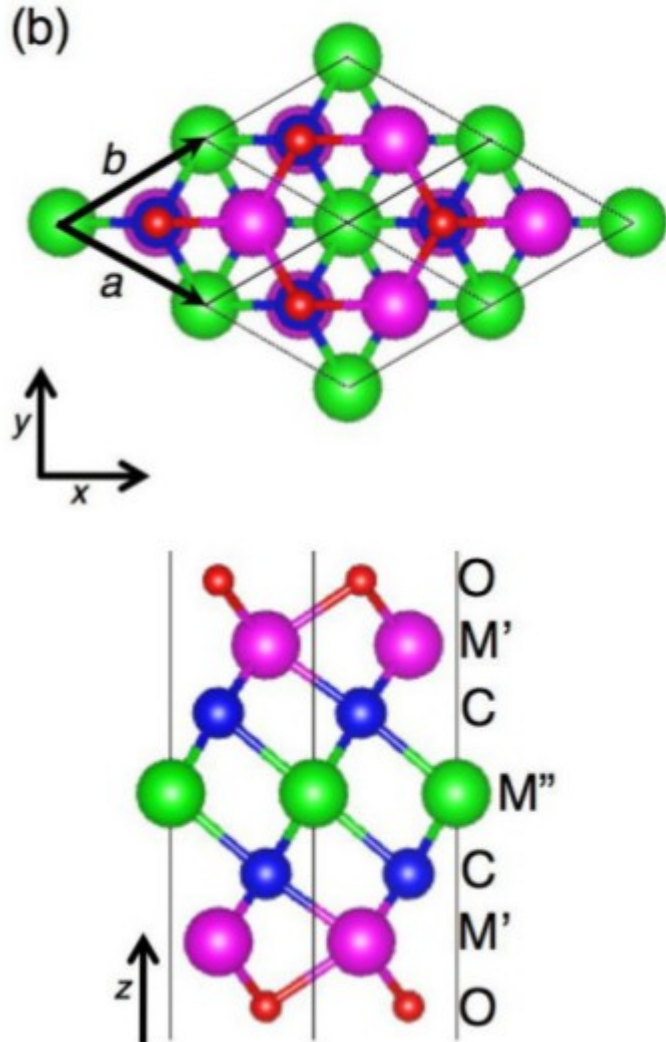
¹Computational Materials Science Research Team, RIKEN Advanced Institute for Computational Science (AICS), Kobe, Hyogo 650-0047, Japan

²International Center for Materials Nanoarchitectonics, National Institute for Materials Science (NIMS), 1-1 Namiki, Tsukuba 305-0044, Ibaraki, Japan

³Computational Condensed Matter Physics Laboratory, RIKEN, Wako, Saitama 351-0198, Japan

⁴Computational Quantum Matter Research Team, RIKEN Center for Emergent Matter Science (CEMS), Wako, Saitama 351-0198, Japan

(Received 27 July 2016; revised manuscript received 7 September 2016; published 30 September 2016)



$M_2MC_2O_2$ ($M = \text{Mo, W}$; $M = \text{Ti, Zr, Hf}$) MXenes are TIs

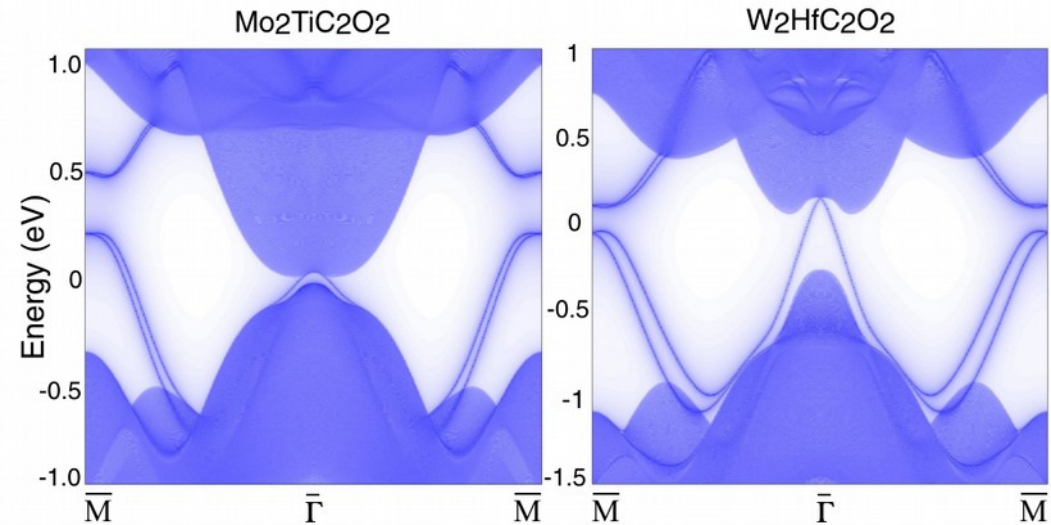
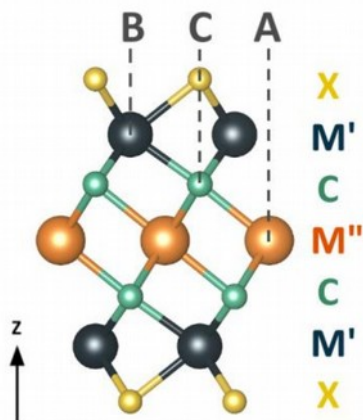


FIG. 4. Edge band structures for $\text{Mo}_2\text{TiC}_2\text{O}_2$ and $\text{W}_2\text{HfC}_2\text{O}_2$. The Fermi energy is located at zero energy.

Search



Yellow X : F, Cl, Br, I, O, or H

Black M' : V, Nb, or Tb

light green C : C

orange M'' : Ti, Hf, or Zr

Group →	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18
Period ↓	1 1 H																	2 He
2	3 Li	4 Be											5 B	6 C	7 N	8 O	9 F	10 Ne
3	11 Na	12 Mg											13 Al	14 Si	15 P	16 S	17 Cl	18 Ar
4	19 K	20 Ca	21 Sc	22 Ti	23 V	24 Cr	25 Mn	26 Fe	27 Co	28 Ni	29 Cu	30 Zn	31 Ga	32 Ge	33 As	34 Se	35 Br	36 Kr
5	37 Rb	38 Sr	39 Y	40 Zr	41 Nb	42 Mo	43 Tc	44 Ru	45 Rh	46 Pd	47 Ag	48 Cd	49 In	50 Sn	51 Sb	52 Te	53 I	54 Xe
6	55 Cs	56 Ba	57 La	* 72 Hf	73 Ta	74 W	75 Re	76 Os	77 Ir	78 Pt	79 Au	80 Hg	81 Tl	82 Pb	83 Bi	84 Po	85 At	86 Rn
7	87 Fr	88 Ra	89 Ac	* 104 Rf	105 Db	106 Sg	107 Bh	108 Hs	109 Mt	110 Ds	111 Rg	112 Cn	113 Nh	114 Fl	115 Mc	116 Lv	117 Ts	118 Og
				* 58 Ce	59 Pr	60 Nd	61 Pm	62 Sm	63 Eu	64 Gd	65 Tb	66 Dy	67 Ho	68 Er	69 Tm	70 Yb	71 Lu	
				* 90 Th	91 Pa	92 U	93 Np	94 Pu	95 Am	96 Cm	97 Bk	98 Cf	99 Es	100 Fm	101 Md	102 No	103 Lr	

Computational Method

Package: Vienna Ab initio simulation package ([VASP 5.4.4](#))

Pseudopotential: Projector augmented wave method ([PAW](#))

Exchange-correction: Generalized Gradient Approximation ([PBE](#))

k-point grid: [12x12x1](#) Gamma-center Monkhorst-Pack

Cut off energy: [400 eV](#)

vacuum space : [~20 Å](#)

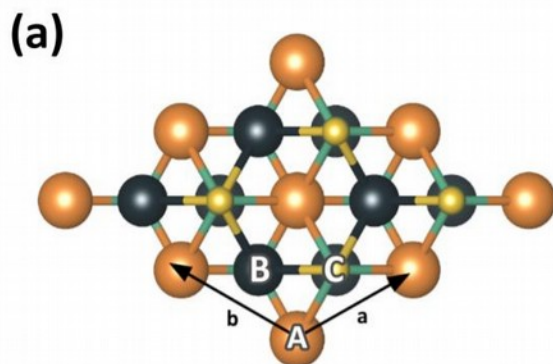
forces : [< 10⁻³ eV/Å](#) in fully relaxed structures

convergence criteria : [10⁻⁶eV](#)

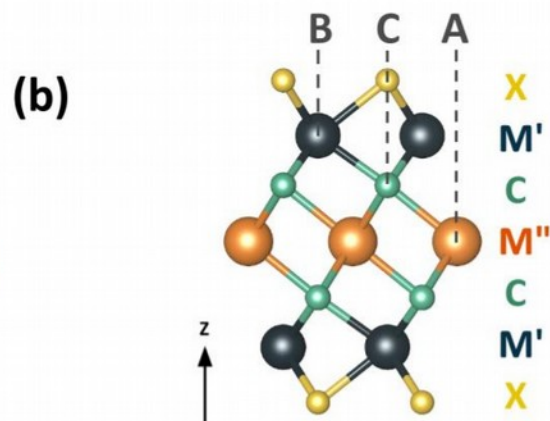
Crystal structure of $M'_2M''C_2X_2$



Top view



Side view

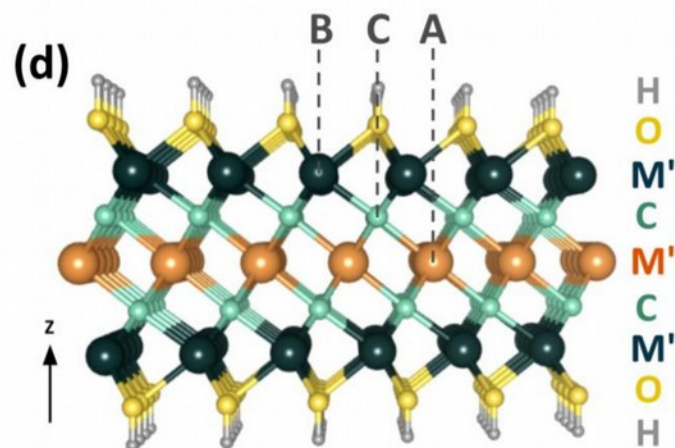
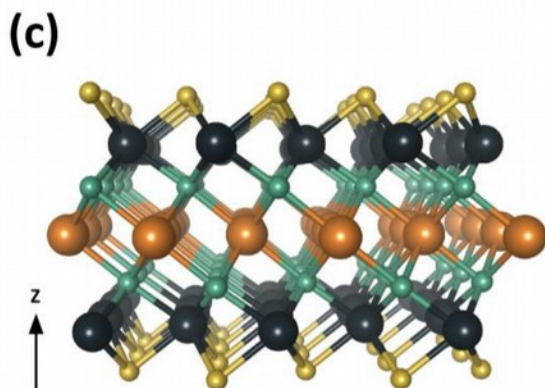


Black M' : V, Nb, or Tb

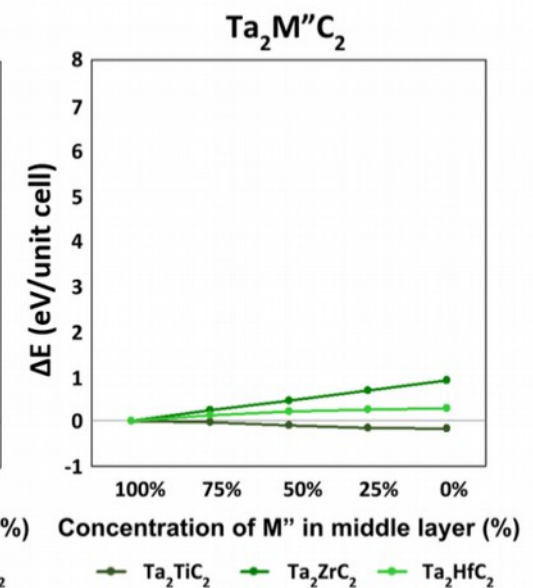
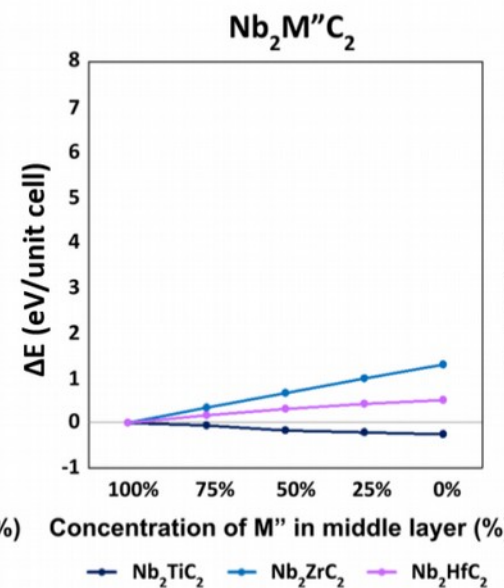
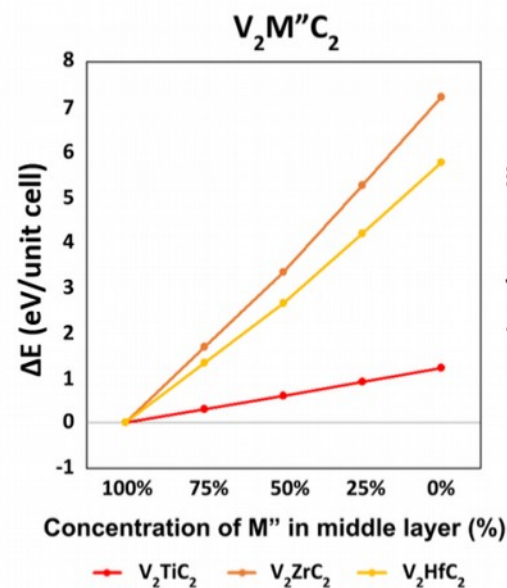
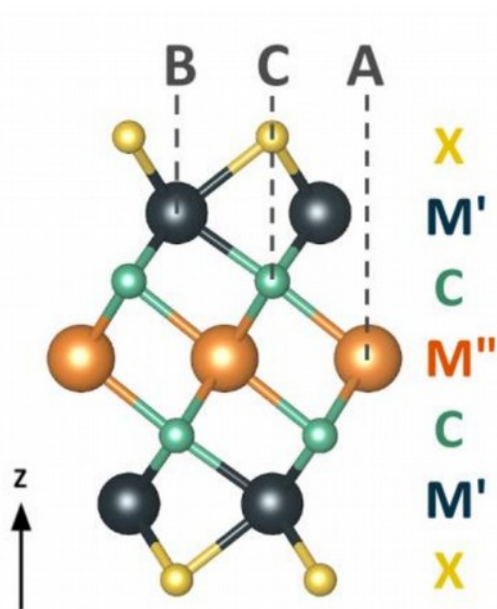
orange M'' : Ti, Hf, or Zr

light green : C

Yellow X : F, Cl, Br, I, O, H, OH



Order Double Transition Metals MXenes



The 100% concentration of M'' in the middle layer corresponds to the fully ordered structure.

Most of them are order, except Nb_2TiC_2 and Ta_2TiC_2 .

$V_2TiC_2X_2$ (X=F, Cl, Br, I, O, OH)

	Lattice constant(Å)	Z_2	System band gap (meV)	Γ -point band gap (meV)
$V_2TiC_2F_2$	2.86	1	37	39
$V_2TiC_2Cl_2$	3.02	1	-187	12
$V_2TiC_2Br_2$	3.10	1	-446	135
$V_2TiC_2I_2$	3.24	1	-463	270
$V_2TiC_2O_2$	2.88	0	-788	14
$V_2TiC_2H_2$	2.88	1	-419	29
$V_2TiC_2(OH)_2$	2.84	1	-151	48

Table 1. The lattice constant, Z_2 topological invariant, system band gap, and Γ -point band gap of $V_2TiC_2X_2$ (X = F, Cl, Br, I, O, H, or OH).

$V_2TiC_2X_2$ (where X = F, Cl, I, Br, H, or OH) are topological semimetals, and only $V_2TiC_2O_2$ is a trivial insulator

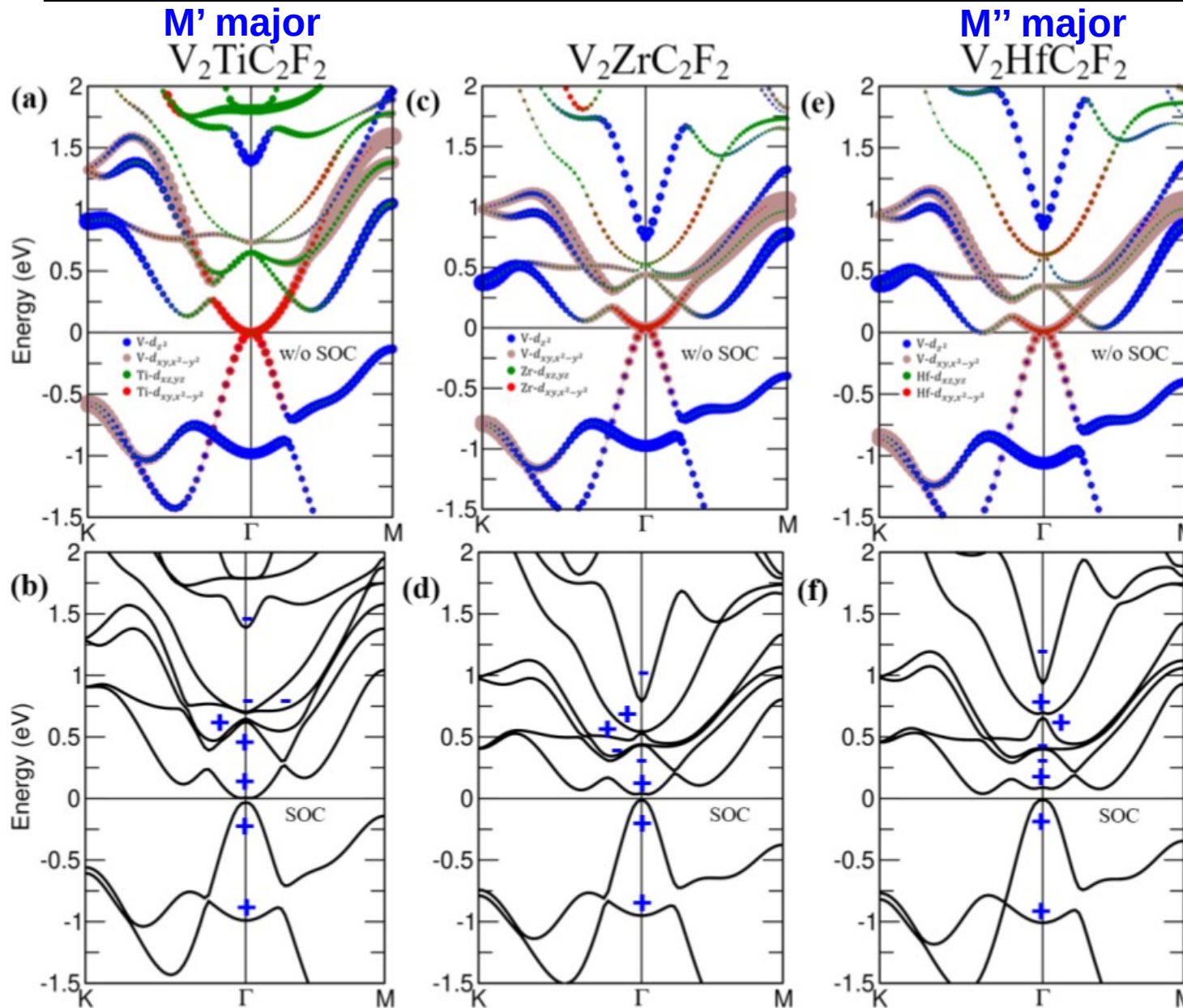
$M'_2M''C_2F_2$ ($M'=V,Nb,Ta$; $M''=Ti,Zr,Hf$)

	Lattice constant (Å)	Z_2	System band gap (meV) PBE(HSE06)	Γ -point band gap (meV) PBE(HSE06)
$V_2TiC_2F_2$	2.86	1	37 (212)	39 (248)
$V_2ZrC_2F_2$	2.99	1	48 (192)	55 (252)
$V_2HfC_2F_2$	2.96	1	49 (295)	101 (389)
$Nb_2TiC_2F_2$	3.00	1	53 (223)	82 (259)
$Nb_2ZrC_2F_2$	3.07	1	4 (139)	110 (263)
$Nb_2HfC_2F_2$	3.04	1	-6 (130)	217 (399)
$Ta_2TiC_2F_2$	3.01	1	5 (319)	207 (483)
$Ta_2ZrC_2F_2$	3.04	1	-70 (49)	278 (489)
$Ta_2HfC_2F_2$	3.05	1	-23 (128)	424 (658)

Table 2. The lattice constant, Z_2 topological invariant, system band gap, and Γ -point band gap by PBE and HSE06 of $M'_2M''C_2F_2$ ($M' = V, Nb, \text{ or } Ta$; $M'' = Ti, Zr, \text{ or } Hf$). The values in the parentheses are obtained by hybrid functional calculations.

Since PBE will underestimate the band gap, HSE06 will give a more accurate band gap. The topological phase is the same in PBE and HSE06 calculations.

Band structures



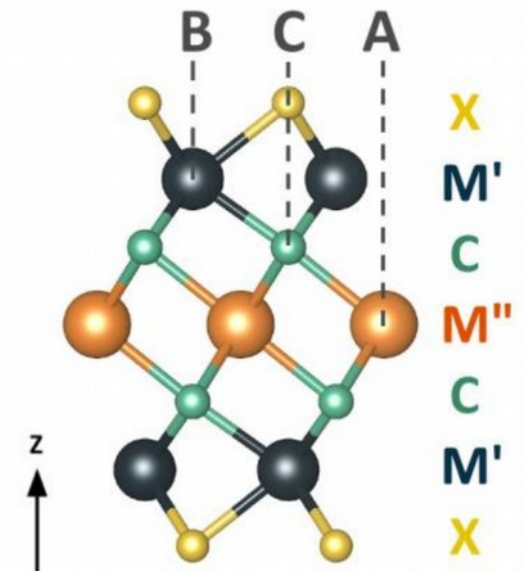
brown M' : $V d_{xy}+d_{x^2-y^2}$

red M'' : $Ti d_{xy}+d_{x^2-y^2}$

At Γ gap

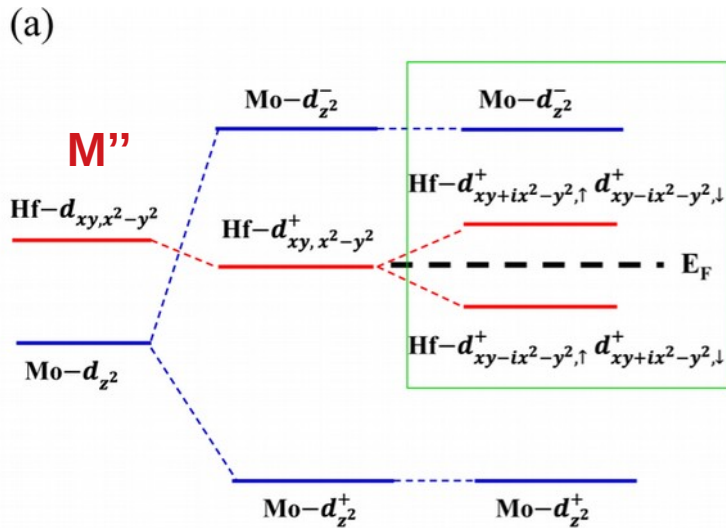
$V_2TiC_2F_2$: $Ti d_{xy}+d_{x^2-y^2}$

$V_2HfC_2F_2$: $V d_{xy}+d_{x^2-y^2}$

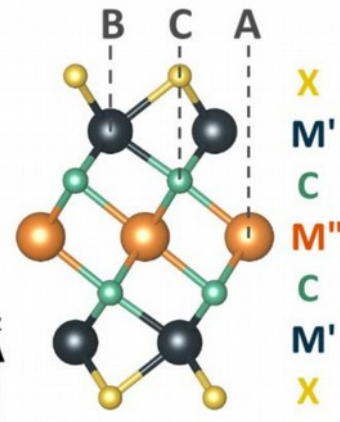
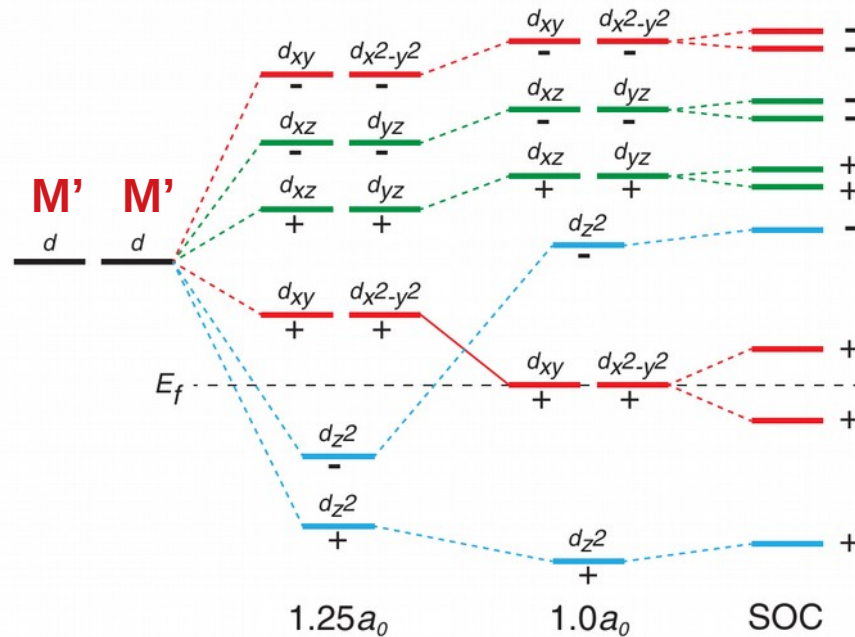


Different mechanism at Γ point

$\text{Mo}_2\text{M}''\text{C}_2\text{O}_2$ ($\text{M}''=\text{Ti}, \text{Zr}, \text{Hf}$)



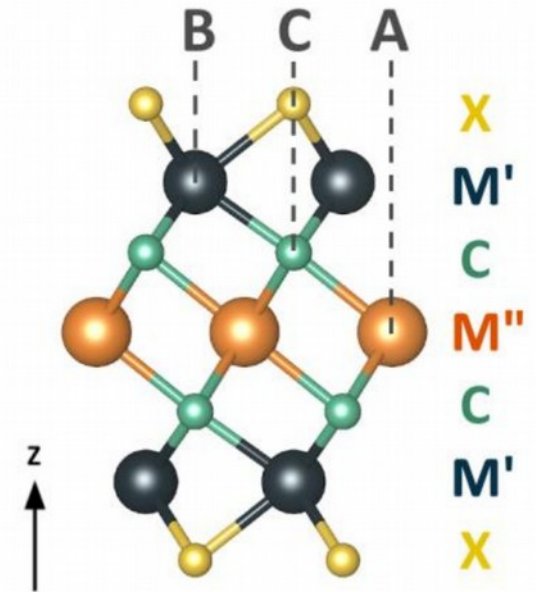
$\text{M}'_2\text{M}''\text{C}_2\text{O}_2$ ($\text{M}'=\text{Mo}, \text{W}$; $\text{M}''=\text{Ti}, \text{Zr}, \text{Hf}$)



Band gaps at the Γ point

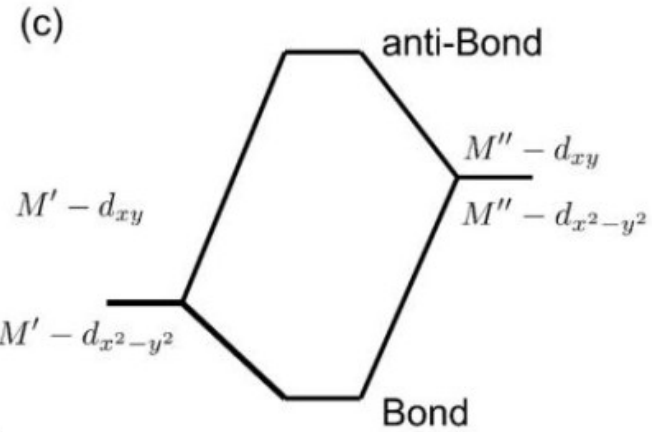
$M'_2M''C_2F_2$	SOC gap (eV) at Γ			$d_{xy} + d_{x^2-y^2}$ orbitals at Γ	
	$M' \& M''$	M'	M''	Contribution from M'	Contribution from M''
$V_2TiC_2F_2$	0.0393	0.0245	0.0120	0.231	0.367
$V_2ZrC_2F_2$	0.0553	0.0258	0.0254	0.258	0.232
$V_2HfC_2F_2$	0.1014	0.0203	0.0753	0.244	0.174
$Nb_2TiC_2F_2$	0.0821	0.0654	0.0141	0.182	0.400
$Nb_2ZrC_2F_2$	0.1104	0.0691	0.0372	0.196	0.309
$Nb_2HfC_2F_2$	0.2167	0.0692	0.1416	0.201	0.298
$Ta_2TiC_2F_2$	0.2070	0.1871	0.0163	0.142	0.462
$Ta_2ZrC_2F_2$	0.2777	0.2268	0.0458	0.173	0.369
$Ta_2HfC_2F_2$	0.4237	0.2513	0.1613	0.190	0.334

Gap induced by M' and M''

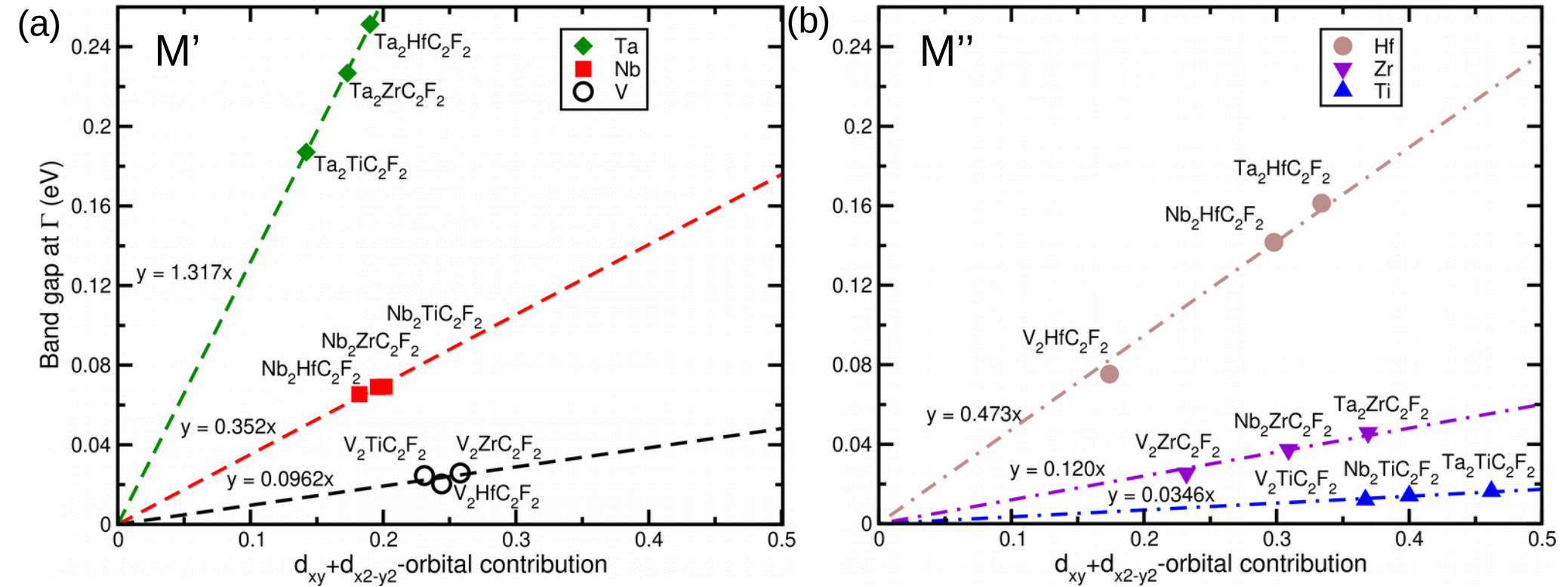


Band gaps at the Γ point

$M'_2M''C_2F_2$	SOC gap (eV) at Γ			$d_{xy} + d_{x^2-y^2}$ orbitals at Γ	
	$M' \& M''$	M'	M''	Contribution from M'	Contribution from M''
$V_2TiC_2F_2$	0.0393	0.0245	0.0120	0.231	0.367
$V_2ZrC_2F_2$	0.0553	0.0258	0.0254	0.258	0.232
$V_2HfC_2F_2$	0.1014	0.0203	0.0753	0.244	0.174
$Nb_2TiC_2F_2$	0.0821	0.0654	0.0141	0.182	0.400
$Nb_2ZrC_2F_2$	0.1104	0.0691	0.0372	0.196	0.309
$Nb_2HfC_2F_2$	0.2167	0.0692	0.1416	0.201	0.298
$Ta_2TiC_2F_2$	0.2070	0.1871	0.0163	0.142	0.462
$Ta_2ZrC_2F_2$	0.2777	0.2268	0.0458	0.173	0.369
$Ta_2HfC_2F_2$	0.4237	0.2513	0.1613	0.190	0.334



Band gaps at the Γ point

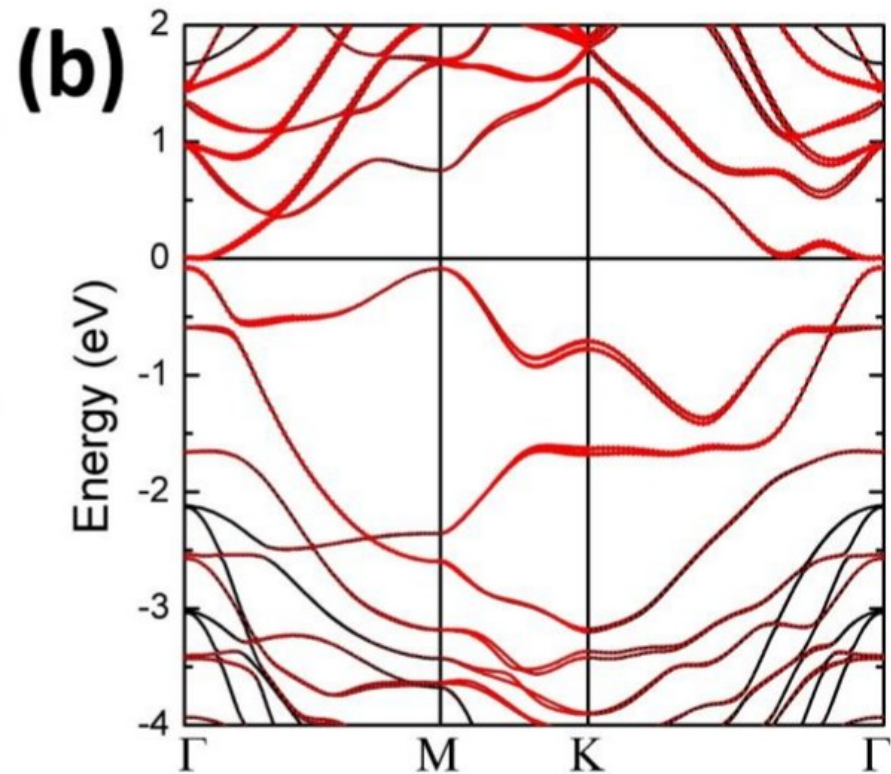
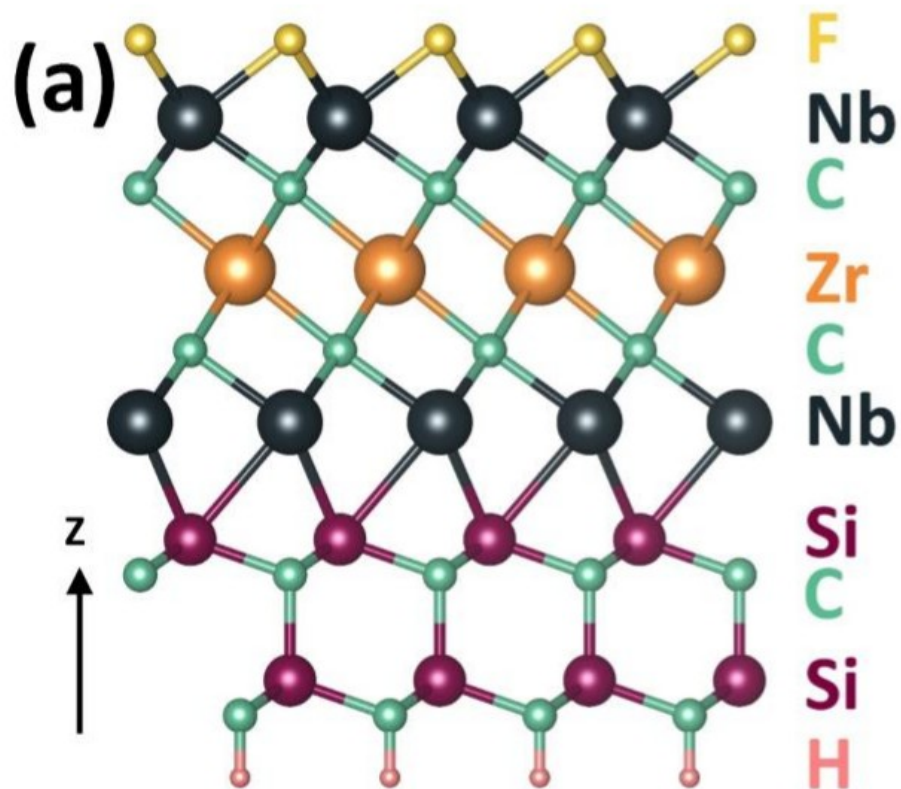


linear combination

$$Gap \sim \langle d_{M'} | \Psi \rangle^2 \lambda_{SOC}(M') + \langle d_{M''} | \Psi \rangle^2 \lambda_{SOC}(M'')$$

The substrate supported MXenes

SiC(0001)-supported Nb₂ZrC₂F₂



Red dots : the contribution from Nb and Zr atoms

Conclusions

- Some ordered double-transition metal MXenes, $M'_2M''C_2X_2$ ($M' = V, Nb,$ or Ta ; $M'' = Ti, Zr,$ or Hf ; $X = F, Cl, Br, I, H,$ or OH) are topological insulators by first-principles calculation.
- Atomic and orbital contribution analyses show that majority of the contribution in the bands near fermi level at the Γ -point are from d_{xy} and $d_{x^2-y^2}$ orbitals of the transition metal M' and M'' .
- Propose SiC(0001) as a candidate substrate for material realization